Silicon NPN Power Transistors 2SC4370

DESCRIPTION
·With TO-220F package
·Complement to type 2SA1659
·High transition frequency

APPLICATIONS
·High voltage applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

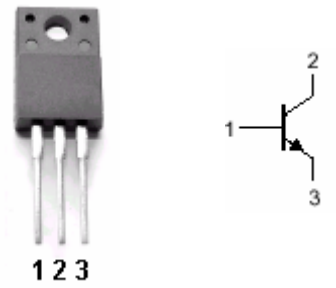

Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	160	V
V_{CEO}	Collector-emitter voltage	Open base	160	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_B	Base current		0.15	A
P_C	Collector dissipation	T_C=25□	20	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ;I_B=0	160			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=0.5A; I_B=50mA			1.5	V
V_{BE}	Base-emitter on voltage	I_C=0.5A;V_{CE}=5V			1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=160V; I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			1.0	μA
h_{FE}	DC current gain	I_C=0.1A ; V_{CE}=5V	70		240	
f_T	Transition frequency	I_C=0.1A ; V_{CE}=10V		100		MHz
C_{OB}	Collector output capacitance	f=1MHz;V_{CB}=10V		25		pF

◆ **h_{FE} Classifications**

O	Y
70-140	120-240

PACKAGE OUTLINE

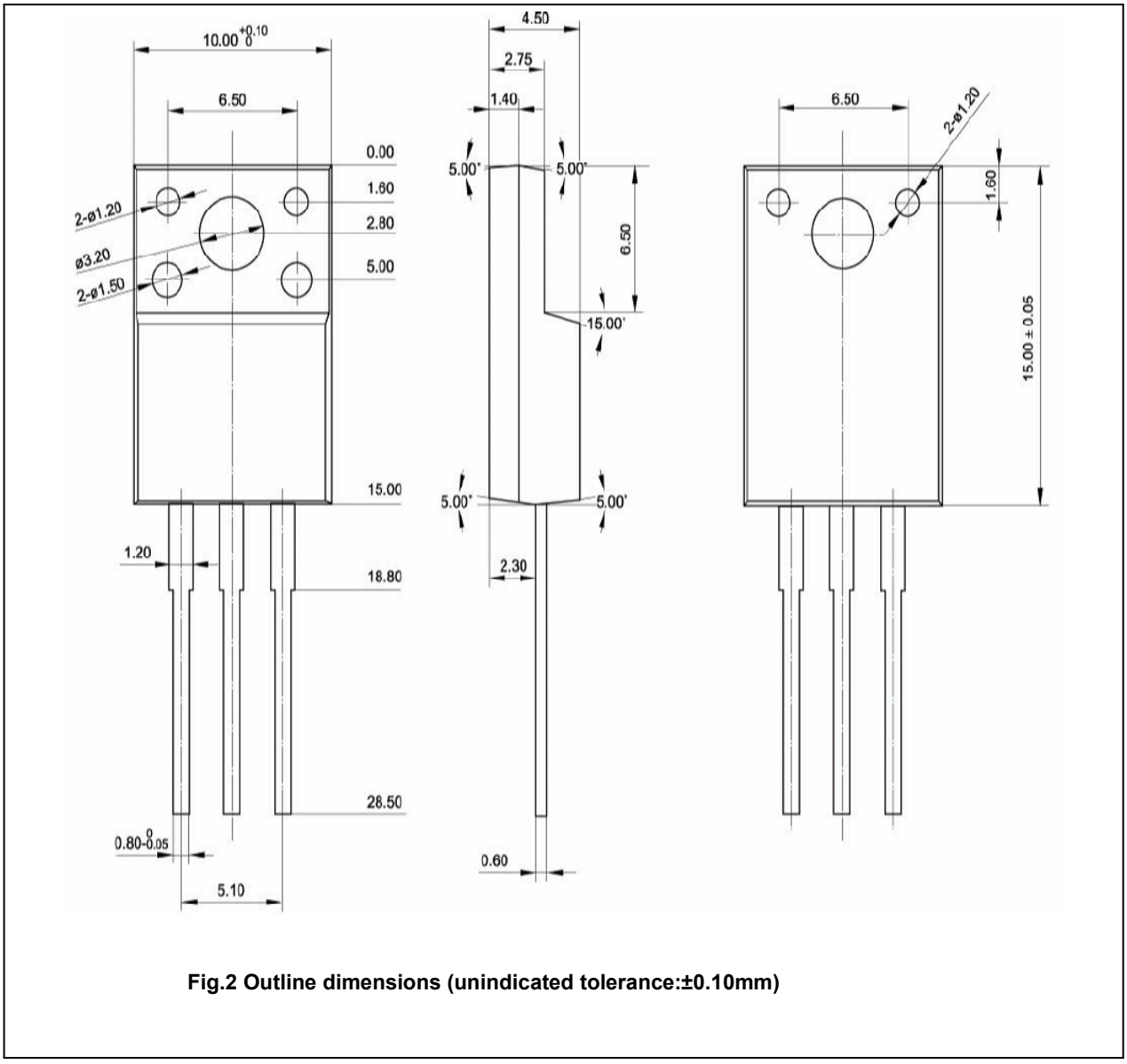

Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)